

Letao Zhang

List of Publications by Year in descending order

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32
times ranked

351
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural, optical and electrical properties of sputtered Nb doped TiO ₂ transparent conductive films. , 2019, , .		0
2	Implementation of Self-Aligned Top-Gate Amorphous Zinc Tin Oxide Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 901-904.	2.2	15
3	Gate Insulator Influences on the Electrical Performance of Back-Channel-Etch Amorphous Zinc Tin Oxide (a-ZTO) Thin Film Transistors. , 2019, , .		0
4	Nonlinear photocurrent-intensity behavior of amorphous InZnO thin film transistors. Applied Physics Letters, 2018, 112, .	1.5	8
5	Room-Temperature-Processed Flexible Amorphous InGaZnO Thin Film Transistor. ACS Applied Materials & Interfaces, 2018, 10, 25850-25857.	4.0	36
6	P-1.6: Effect of Deposition Condition of Passivation Layer on the Performance of Self-Aligned Top-Gate a-IGZO TFTs. Digest of Technical Papers SID International Symposium, 2018, 49, 535-537.	0.1	1
7	Ti Film Thickness Influences on the Back Channel Etched Amorphous InGaZnO Thin Film Transistors. , 2018, , .		0
8	24.5: Back-Channel-Etched a-IGZO TFTs with TiO ₂ :Nb Protective Layer. Digest of Technical Papers SID International Symposium, 2018, 49, 263-266.	0.1	0
9	Dynamic Threshold Voltage Modulation in Double-Gate Indium-Gallium-Zinc Oxide Thin-Film Transistors: Influence of the Active Layer Thickness. , 2018, , .		1
10	P-6.1: Asymmetric Effects of Gate-Bias Stress Voltage on the Stability under Positive and Negative Gate-Bias Stress of a-IGZO TFTs. Digest of Technical Papers SID International Symposium, 2018, 49, 597-600.	0.1	2
11	P-13: Electrical Characteristics and Stability of Double-Gate a-IGZO Thin Film Transistors with Self-Aligned Top-Gate. Digest of Technical Papers SID International Symposium, 2018, 49, 1227-1230.	0.1	0
12	Oxygen Adsorption Effect of Amorphous InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2017, 38, 465-468.	2.2	14
13	Source-drain resistance characteristics of back-channel etched amorphous InGaZnO thin film transistors with TiO ₂ :Nb protective layer. Materials Science in Semiconductor Processing, 2017, 68, 147-151.	1.9	7
14	Nb Doped TiO ₂ -Protected Back-Channel-Etched Amorphous InGaZnO Thin Film Transistors. IEEE Electron Device Letters, 2017, 38, 213-216.	2.2	13
15	Oxide Thin-Film Transistors With IMO and IGZO Stacked Active Layers for UV Detection. IEEE Journal of the Electron Devices Society, 2017, 5, 504-508.	1.2	22
16	P-8: Photocurrent Characteristics of Amorphous MgInO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1254-1257.	0.1	1
17	P-9: Parylene / Al ₂ O ₃ Double Layer Passivated Amorphous InGaZnO Thin-Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1258-1261.	0.1	7
18	P-20: Effects of N ₂ O Plasma Treatment Time on the Performance of Self-Aligned Top-Gate amorphous oxide Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1299-1302.	0.1	11

#	ARTICLE	IF	CITATIONS
19	Pâ€21: The Effect of Thermal Annealing Sequence on the Performance of Selfâ€Aligned Topâ€Gate aâ€IGZO TFTs. Digest of Technical Papers SID International Symposium, 2017, 48, 1303-1306.	0.1	1
20	Oxygen Interstitial Creation in a-IGZO Thin-Film Transistors Under Positive Gate-Bias Stress. IEEE Electron Device Letters, 2017, 38, 1252-1255.	2.2	41
21	TiO<inf>2</inf>:Nb film thickness influences on the amorphous InGaZnO thin film transistors with Mo/TiO2:Nb source-drain electrodes. , 2017, , .		0
22	Impact of sputtering power of source/drain metal on performances of a-IGZO thin film transistors fabricated using wet back-channel-etch process. , 2017, , .		1
23	ZnSnO thin-film transistors by reactive co-sputtering of Zn and Sn metal targets. , 2017, , .		1
24	Structure and stoichiometry evolution of sputtered Nb doped TiO2 films induced by O2 pressure variation during postannealing process. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	7
25	Oxygen partial pressure and annealing temperature influence on the performance of back-channel-etch zinc tin oxide thin film transistors. , 2016, , .		1
26	Amorphous Indium Tin Oxide Thin-Film Transistors Fabricated by Cosputtering Technique. IEEE Transactions on Electron Devices, 2016, 63, 1072-1077.	1.6	18
27	Pâ€9: Improved Electrical Stability of Doubleâ€Gate aâ€IGZO TFTs. Digest of Technical Papers SID International Symposium, 2015, 46, 1151-1154.	0.1	5
28	Back Channel Anodization Amorphous Indium Gallium Zinc Oxide Thin-Film Transistors Process. IEEE Electron Device Letters, 2015, 36, 357-359.	2.2	9
29	Nanocrystalline SnO2 thin films prepared by anodization of sputtered Sn thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	11
30	Study on the transition between p and n types of SnO<inf>x</inf> film deposited by DC sputtering. , 2014, , .		1
31	Fabrication of indium-tin-oxide thin-film transistor using anodization. , 2014, , .		0
32	Impacts of substrate heating schemes on characteristics of amorphous indium-gallium-zinc-oxide (a-IGZO) TFTs fabricated on flexible substrates. , 2014, , .		1